

Silicon PNP Power Transistors

2SA1633

**DESCRIPTION**

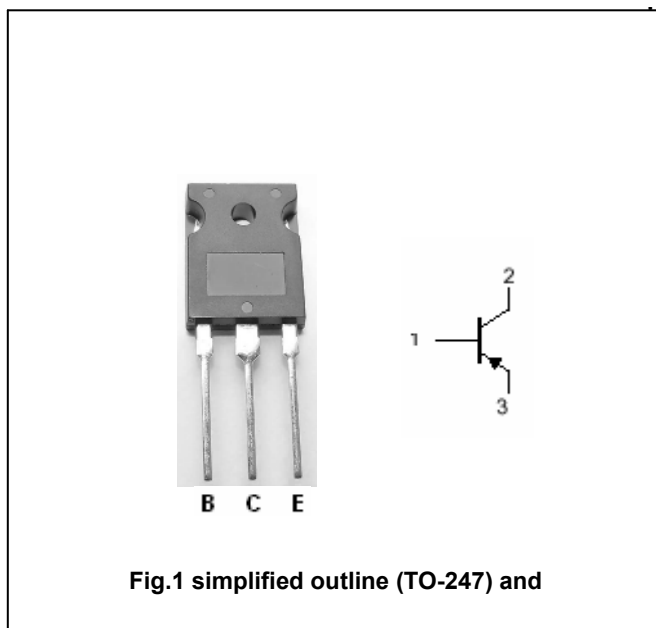
- With TO-247 package
- Complement to type 2SC4278
- High current and high power capability

**APPLICATIONS**

- For audio output applications

**PINNING**

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter



**Absolute maximum ratings(Tc=25°C)**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CBO</sub>	Collector-base voltage	Open emitter	-150	V
V <sub>CEO</sub>	Collector-emitter voltage	Open base	-150	V
V <sub>EBO</sub>	Emitter-base voltage	Open collector	-6	V
I <sub>C</sub>	Collector current		-10	A
P <sub>D</sub>	Total power dissipation	T <sub>C</sub> =25°C	100	W
T <sub>j</sub>	Junction temperature		150	°C
T <sub>stg</sub>	Storage temperature		-55~150	°C

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## CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =-25mA; I <sub>B</sub> =0	-150			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =-5A ; I <sub>B</sub> =-0.5A			-1.5	V
V <sub>BEsat</sub>	Base-emitter saturation voltage	I <sub>C</sub> =-5A ; I <sub>B</sub> =-0.5A			-2.0	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =-150V; I <sub>E</sub> =0			-0.1	mA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =-6V; I <sub>C</sub> =0			-0.1	mA
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =-1A ; V <sub>CE</sub> =-5V	60		320	
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =-1A ; V <sub>CE</sub> =-10V		20		MHz

◆ h<sub>FE</sub> Classifications

D	E	F
60-120	100-200	160-320

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PACKAGE OUTLINE

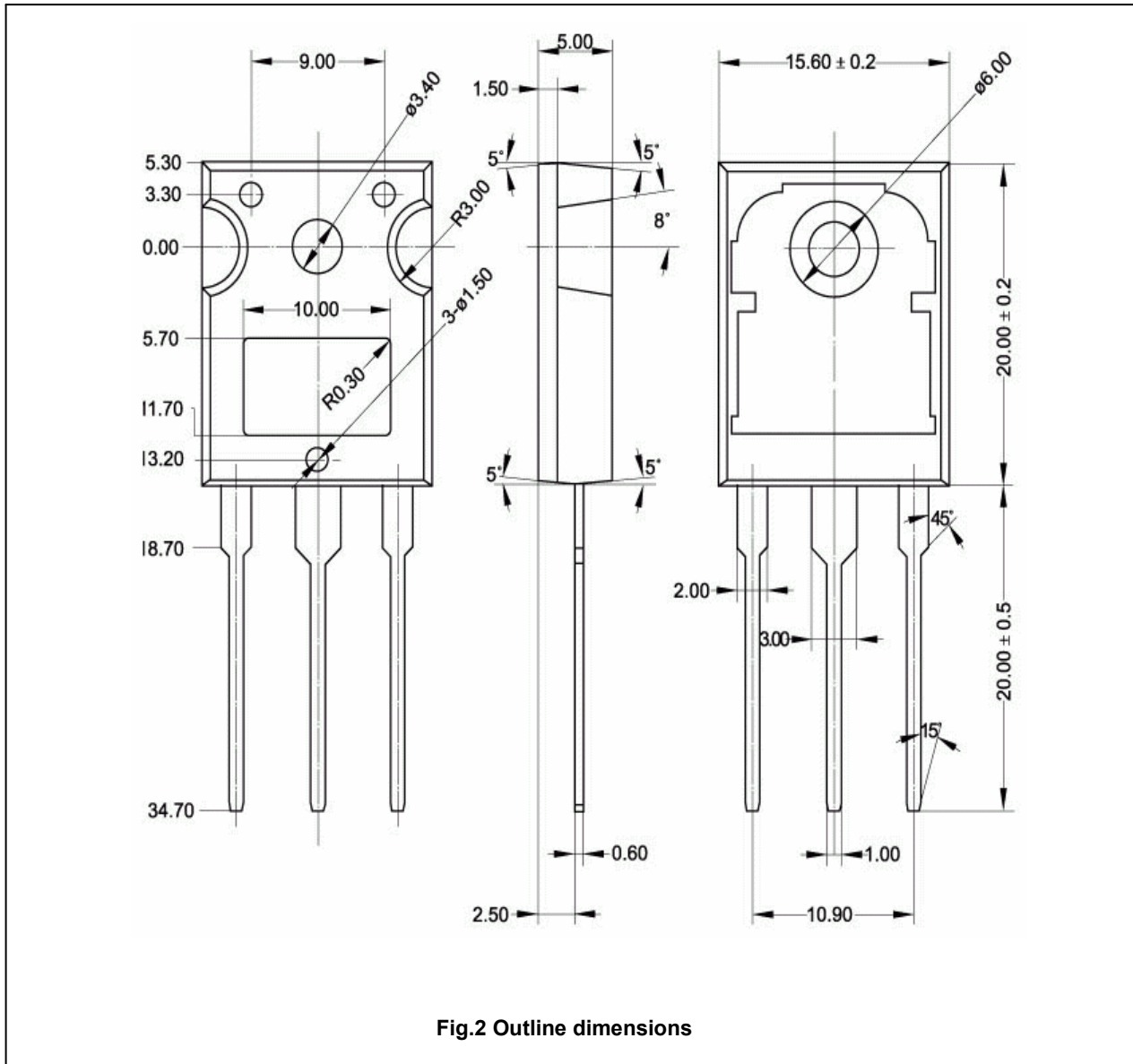


Fig.2 Outline dimensions